

Product data sheet

1. General description

Dual ultrafast power diode in a TO263 (D2PAK) plastic package.

2. Features and benefits

- Ultra low leakage current
- High junction temperature up to 175 °C
- Low on-state loss
- Fast switching
- · Soft recovery characteristic minimizes power consuming oscillations
- High reverse surge capability
- High thermal cycling performance
- · Low thermal resistance

3. Applications

- Home appliance power supply
- Secondary rectification

4. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			300			V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 157 °C; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		10			A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 157 °C; square-wave pulse; per diode		20			A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4				A	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode				A	
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V _F	forward voltage	$I_F = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$		-	-	1.25	V
		$I_{F} = 10 \text{ A}; T_{j} = 125 \text{ °C}; \text{ per diode}; Fig. 6$		-	-	1	V
Dynamic	characteristics		1	1	1		
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _i = 25 °C; per diode; <u>Fig. 7</u>		-	-	25	ns

5. Pinning information

Table 2. F	Pinning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	К	cathode		
3	A2	anode		к К
mb	К	mounting base; connected to cathode		sym125

6. Ordering information

Table 3. Ordering information								
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date		
BYV32EB-300P	TO263	BYV32EB-300PJ	Reel	800	TO263E	26-May-2017		

7. Marking

Table 4. Marking codes						
	Type number	Marking codes				
	BYV32EB-300P	BYV32EB-300P				

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V _{RRM}	repetitive peak reverse voltage		300	V
V_{RWM}	crest working reverse voltage		300	V
V _R	reverse voltage	DC	300	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 157 °C; per diode; Fig. 1; Fig. 2; Fig. 3	10	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 157 °C; square-wave pulse; per diode	20	A
I _{O(AV)}	average output current	δ = 0.5 ; T _{mb} ≤ 155 °C; square-wave pulse; both diodes conducting	20	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	220	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	242	A
T _{stg}	storage temperature		-65 to 175	°C
Tj	junction temperature		175	°C







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9. Thermal characteristics

	able 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
$R_{th(j-mb)}$	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5		-	-	1.5	K/W	
	mounting base	with heatsink compound; both diodes conducting; Fig. 5		-	-	0.85	K/W	
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	50	-	K/W	



Dual ultrafast power diode

10. Characteristics

Table 7. Cl	naracteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	racteristics						
V _F	forward current	I _F = 10 A; T _j = 25 °C; per diode; <u>Fig. 6</u>		-	-	1.25	V
		$I_{F} = 10 \text{ A}; T_{j} = 125 \text{ °C}; \text{ per diode}; Fig. 6$		-	-	1	V
I _R	reverse current	V_R = 300 V; T_j = 25 °C; per diode		-	-	20	μA
		V_{R} = 300 V; T _j = 125 °C; per diode		-	-	300	μA
Dynamic	characteristics						
Q _r	reverse charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	9	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	-	35	ns
		I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _j = 25 °C; per diode; <u>Fig. 7</u>		-	-	25	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	25	-	ns
		I _F = 10 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; per diode; <u>Fig. 7</u>		-	33	-	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	0.7	-	A
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_J = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	1.1	-	A
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	2.8	-	A
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; \text{ per diode}; Fig. 7$		-	-	8	A



11. Package outline



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Dual ultrafast power diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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